

HEXFET® Power MOSFET

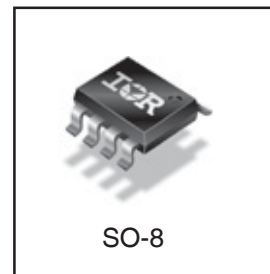
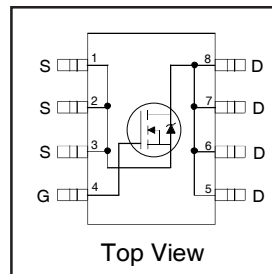
Applications

- High Frequency DC-DC Converters with Synchronous Rectification
- Lead-Free

V_{DSS}	R_{DS(on)} max	I_D
20V	0.0065Ω	16A

Benefits

- Ultra-Low R_{DS(on)} at 4.5V V_{GS}
- Low Charge and Low Gate Impedance to Reduce Switching Losses
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-to-Source Voltage	± 12	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	16	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	13	
I _{DM}	Pulsed Drain Current ^①	130	
P _D @ T _A = 25°C	Maximum Power Dissipation ^③	2.5	W
P _D @ T _A = 70°C	Maximum Power Dissipation ^③	1.6	W
	Linear Derating Factor	0.02	W/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
R _{θJA}	Maximum Junction-to-Ambient ^④	50	°C/W

Typical SMPS Topologies

- Telecom 48V Input Converters with Logic-Level Driven Synchronous Rectifiers

Notes ① through ④ are on page 8

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IRF7456PbF

International
IR Rectifier

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.024	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.0047	0.0065	Ω	V _{GS} = 10V, I _D = 16A ③
		—	0.0057	0.0075		V _{GS} = 4.5V, I _D = 13A ③
		—	0.011	0.020		V _{GS} = 2.8V, I _D = 3.5A ③
V _{GS(th)}	Gate Threshold Voltage	0.6	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 16V, V _{GS} = 0V
		—	—	100		V _{DS} = 16V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -12V

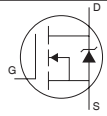
Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	44	—	—	S	V _{DS} = 10V, I _D = 16A
Q _g	Total Gate Charge	—	41	62	nC	I _D = 16A
Q _{gs}	Gate-to-Source Charge	—	9.7	15		V _{DS} = 16V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	18	27		V _{GS} = 5.0V, ③
t _{d(on)}	Turn-On Delay Time	—	20	—	ns	V _{DD} = 10V
t _r	Rise Time	—	25	—		I _D = 1.0A
t _{d(off)}	Turn-Off Delay Time	—	50	—		R _G = 6.0Ω
t _f	Fall Time	—	52	—		V _{GS} = 4.5V ③
C _{iss}	Input Capacitance	—	3640	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1570	—		V _{DS} = 15V
C _{rss}	Reverse Transfer Capacitance	—	330	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	250	mJ
I _{AR}	Avalanche Current①	—	16	A
E _{AR}	Repetitive Avalanche Energy①	—	0.25	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	130		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 2.5A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	48	72	ns	T _J = 25°C, I _F = 2.5A
Q _{rr}	Reverse Recovery Charge	—	74	110	nC	di/dt = 100A/μs ③

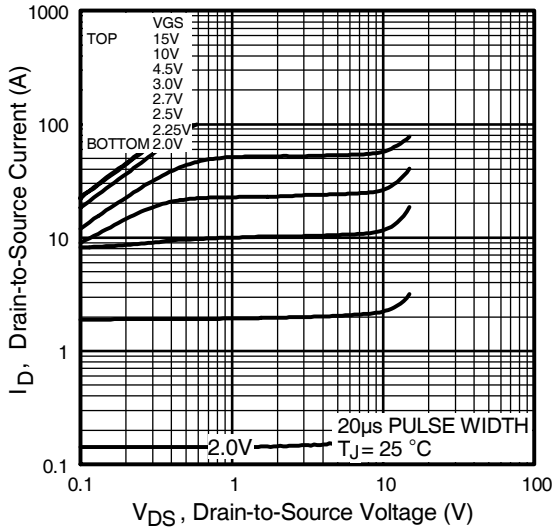


Fig 1. Typical Output Characteristics

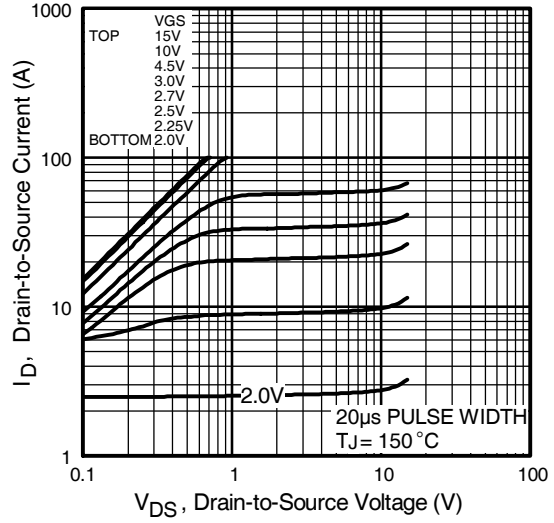


Fig 2. Typical Output Characteristics

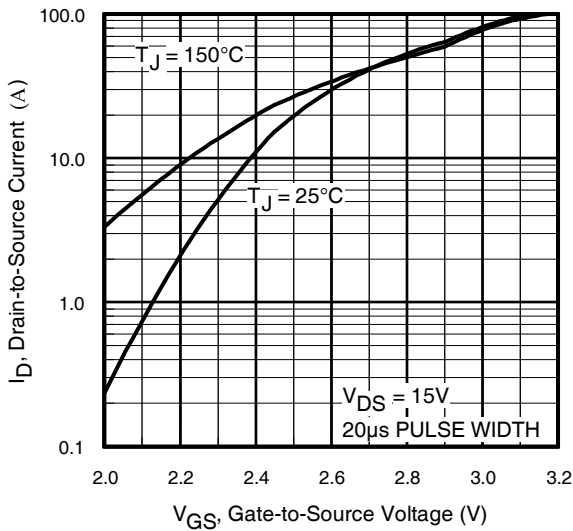


Fig 3. Typical Transfer Characteristics

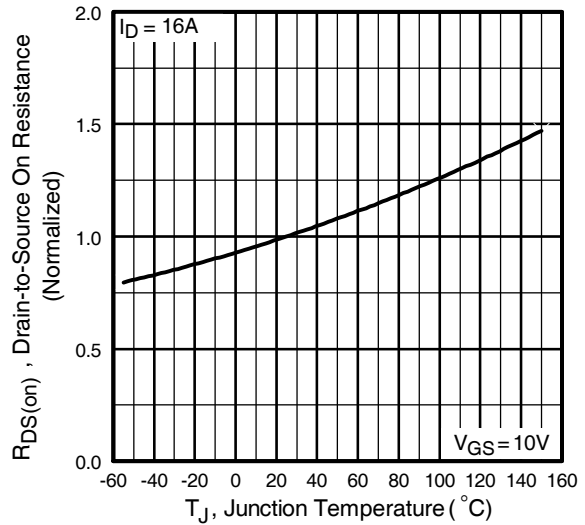


Fig 4. Normalized On-Resistance Vs. Temperature

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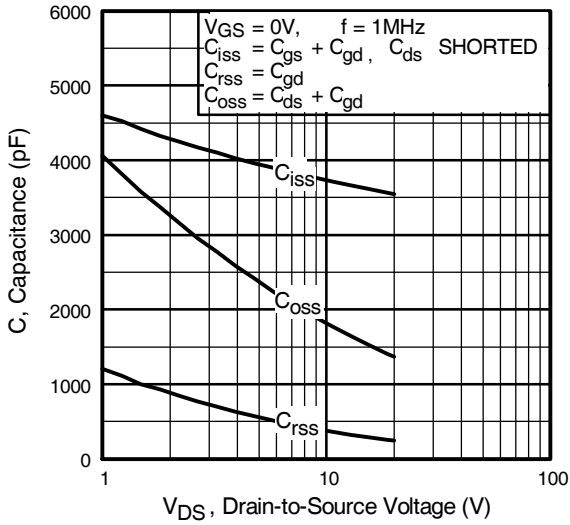


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

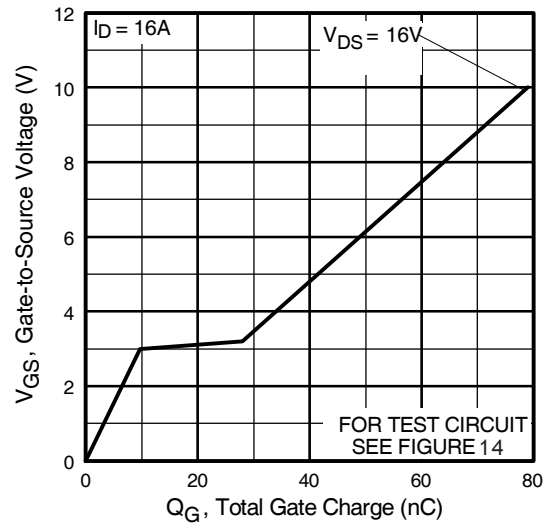


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

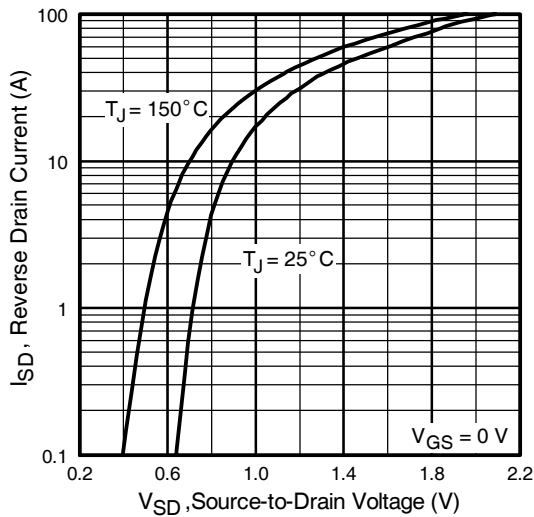


Fig 7. Typical Source-Drain Diode Forward Voltage

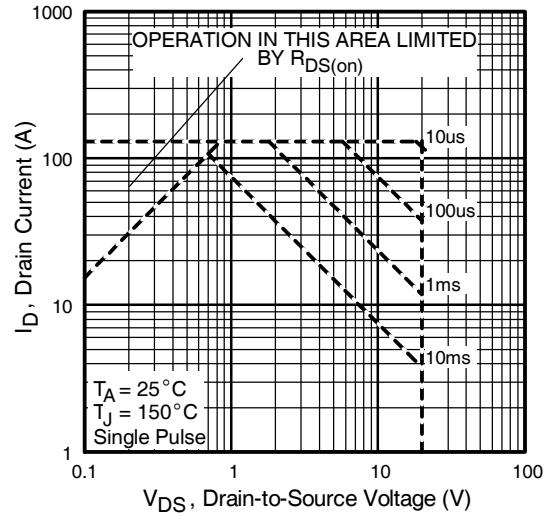


Fig 8. Maximum Safe Operating Area

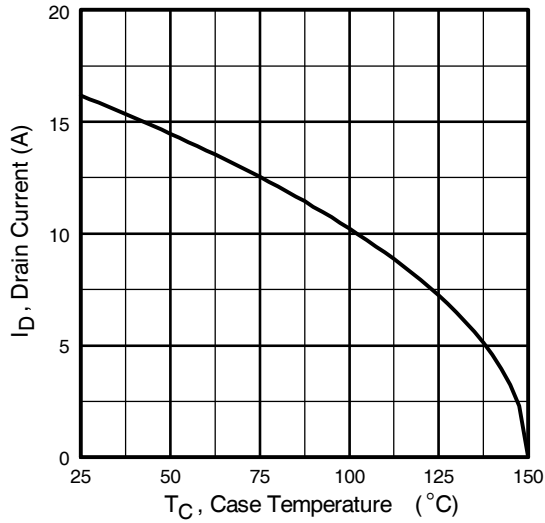


Fig 9. Maximum Drain Current Vs. Case Temperature

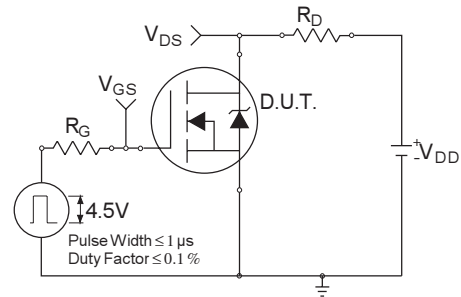


Fig 10a. Switching Time Test Circuit

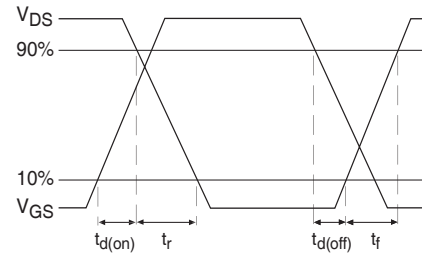


Fig 10b. Switching Time Waveforms

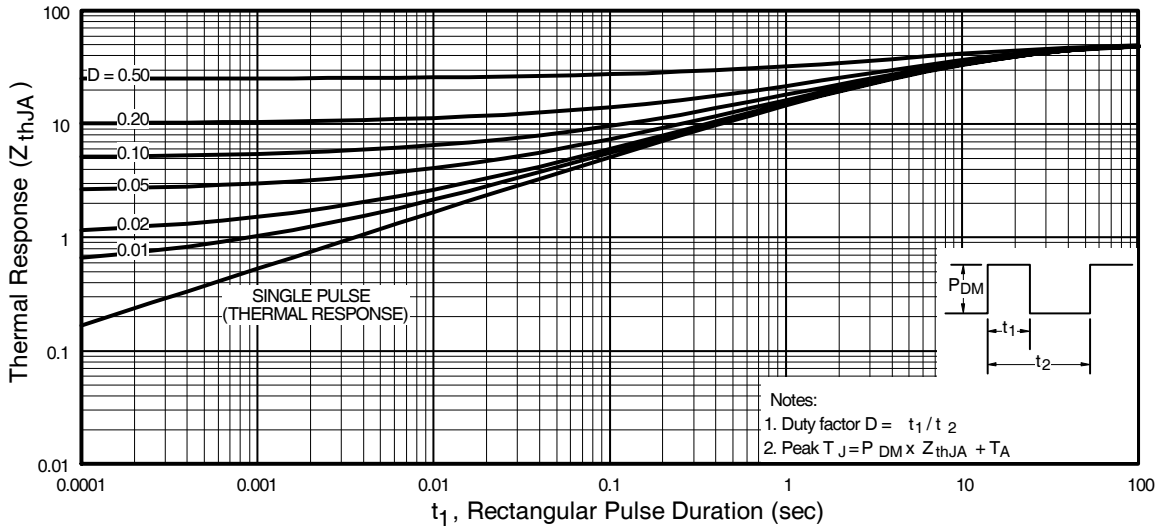


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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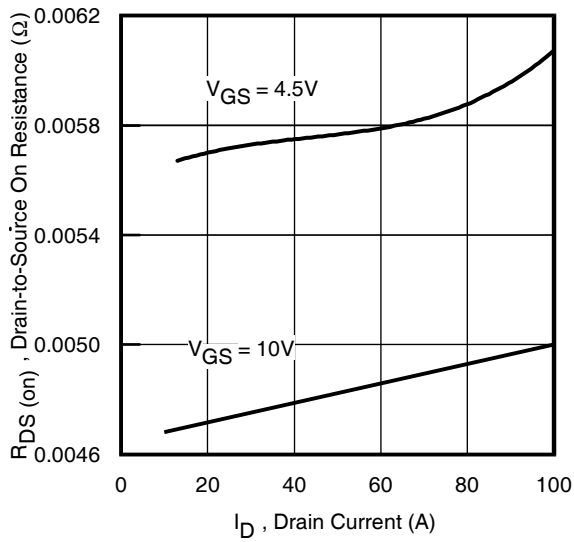


Fig 12. On-Resistance Vs. Drain Current

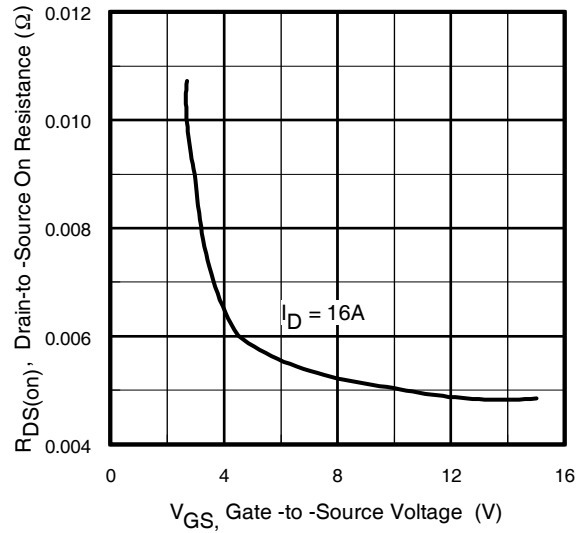


Fig 13. On-Resistance Vs. Gate Voltage

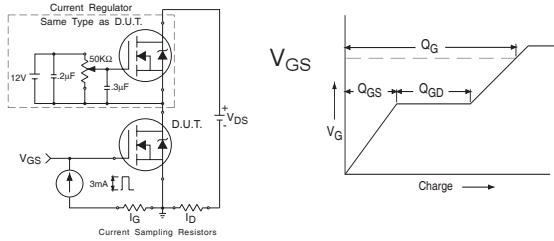


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

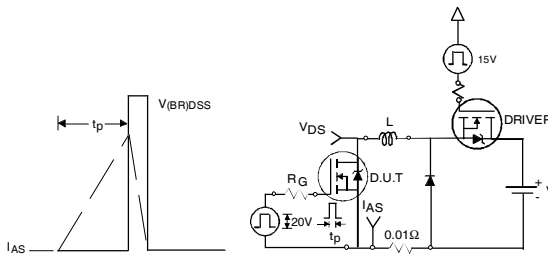


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

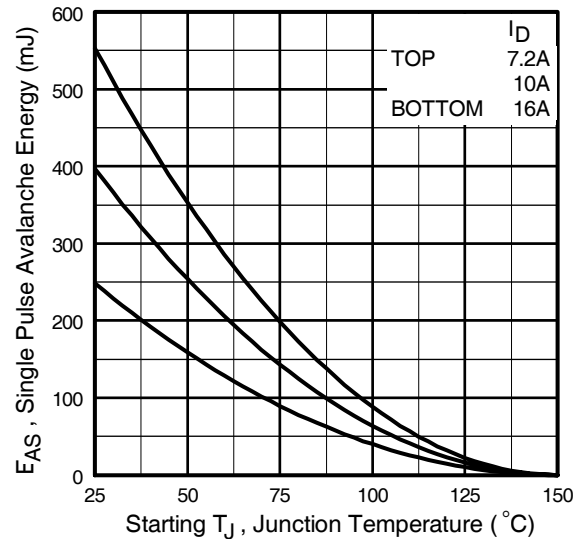
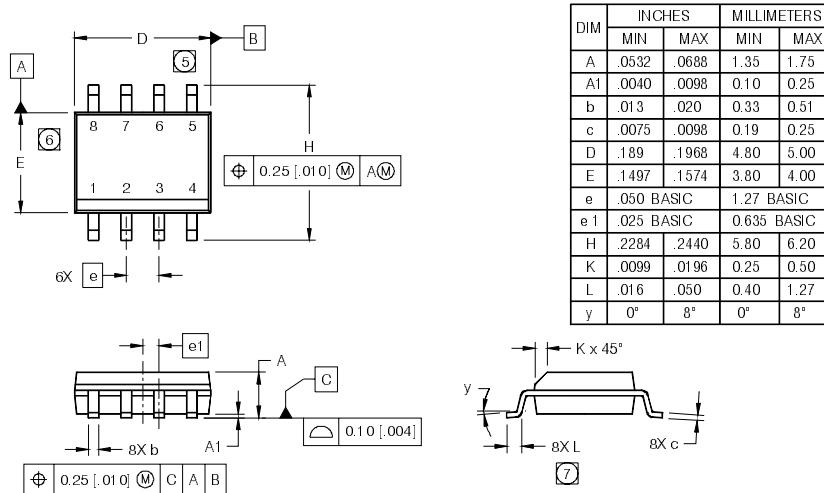


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Outline (MOSFET & Fetky)

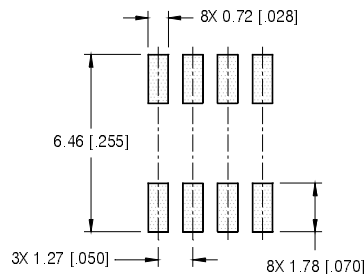
Dimensions are shown in millimeters (inches)



NOTES:

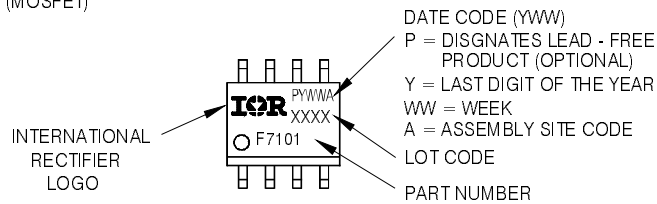
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



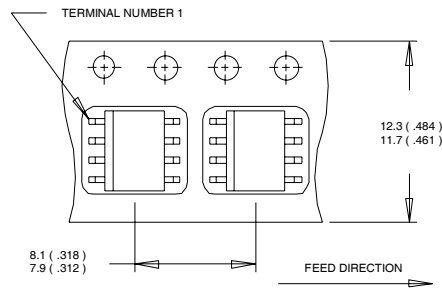
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

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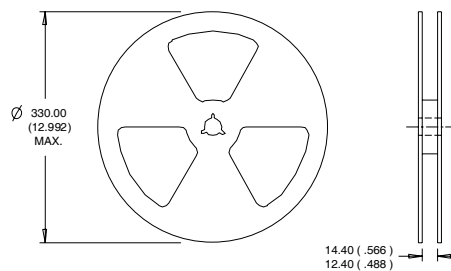
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SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION - MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION - MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 2.0\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 16\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10$ sec

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

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IR Rectifier

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TAC Fax: (310) 252-7903

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